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540171 -- Patent Information

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Abstract	<p>A method for manufacturing high-power light emitting diode that has a metal reflection layer and uses an electroplating method to form a metal substrate is disclosed in the present invention. In the invention, since a metal reflection layer is used such that light absorption problem of substrate can be avoided and the light emitting brightness also can be raised apparently. In addition, P and N electrodes can be formed respectively on a vertical structure of both upper and lower sides of the light emitting diode. Furthermore, a semiconductor substrate is changed into a metal substrate so as to greatly improve the heat dissipation characteristic of the light emitting diode and make the light emitting diode capable of being operated at a higher current.</p>		